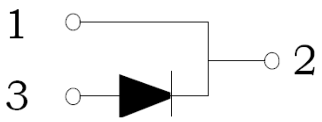
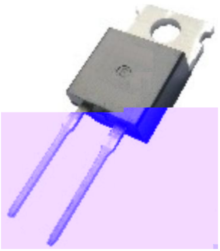
TO-220AC
Ultrafast Recovery Diode in a TO-220AC Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.





PIN1 2 Cathode PIN 3 Anode

See Marking Instructions

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Average Forward Current	I_F	1 × 20	A
Peak forward surge current	I_{FSM}	250	A
Typical Thermal Resistance Junction to Case	R_{Jc}	2.8	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

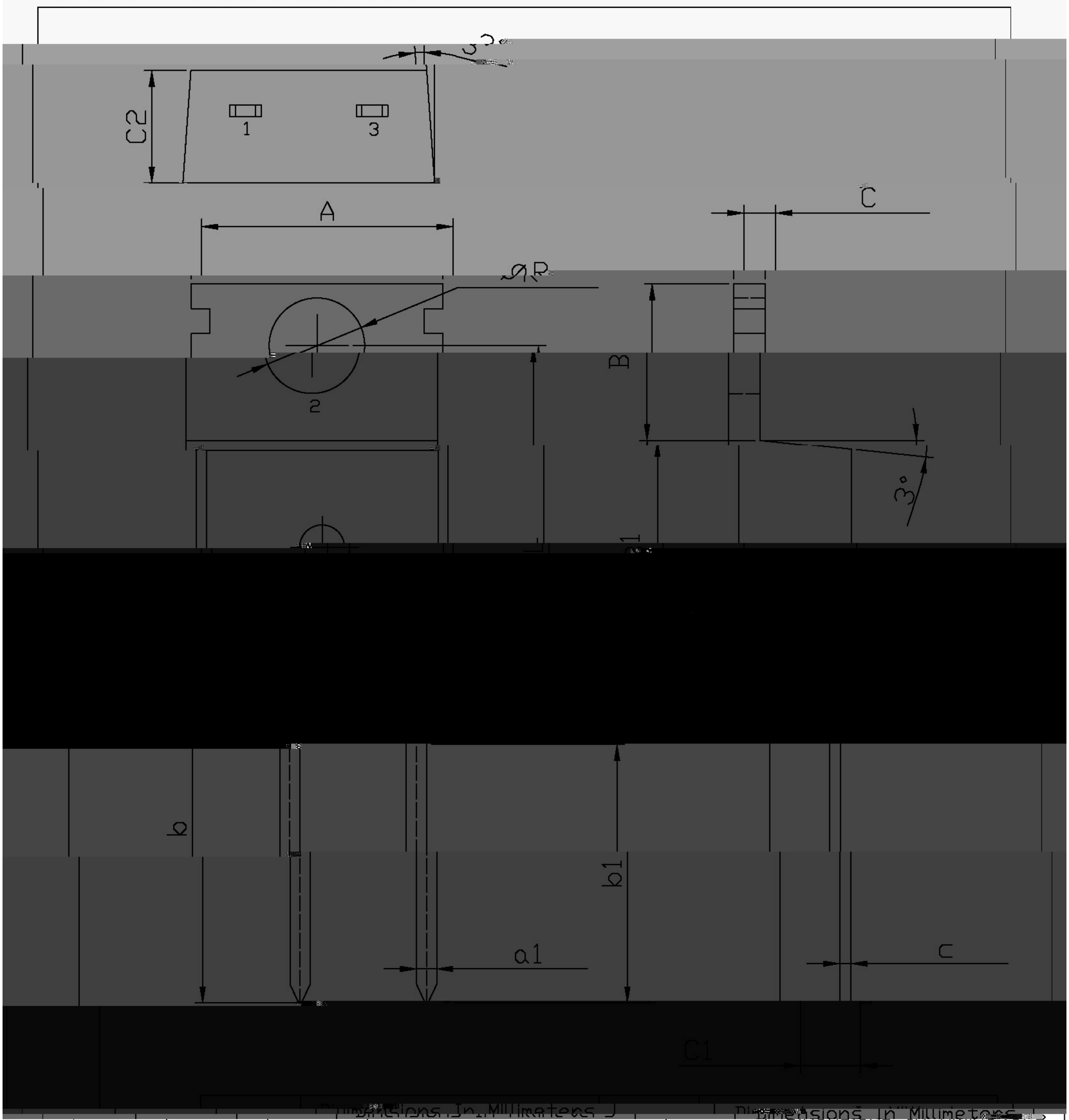
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F=5.0A T_C=25			1.35	V
		I_F=5.0A T_C=150			1.15	
		I_F=20A T_C=25			1.65	
		I_F=20A T_C=150			1.25	
Instantaneous Reverse Current(Note1)	I_R	V_R=600V T_a=25			0.25	mA
		V_R=420V T_a=150			1.0	
		V_R=600V T_a=150			2.0	
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A			50	ns

/Notes

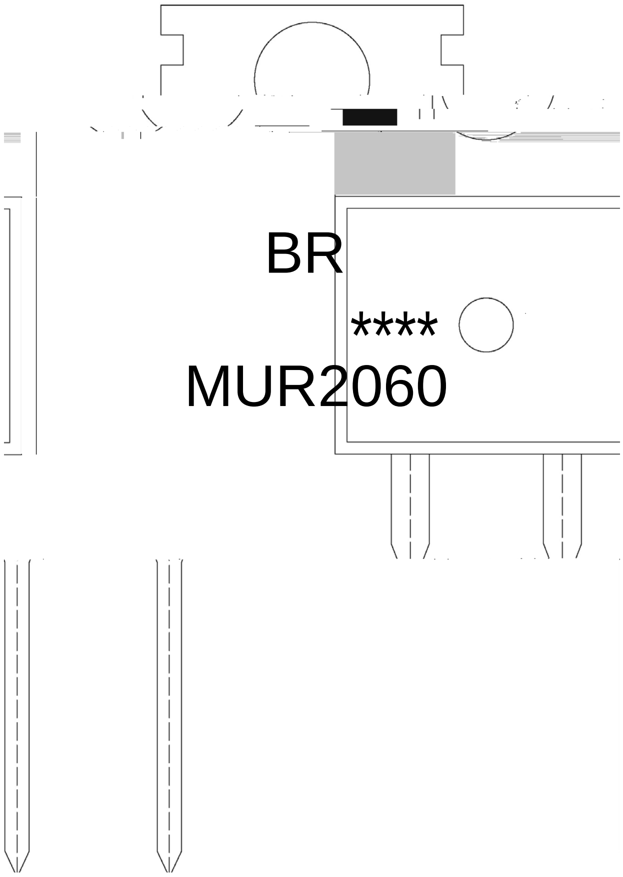
1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip

TO-220AC

Unit:mm



	Dimensions In Millimeters			Dimensions In Millimeters	
Symbol	Min	Max	Symbol	Min	Max
A	9.8	10.2	B	6.3	6.7
R	3.56	3.64	B1	9.0	9.4
b1	9.8	10.6	C	0.4	0.6
a	1.22	1.32	C2	4.3	4.7
a1	0.7	0.9			



BR

MUR2060

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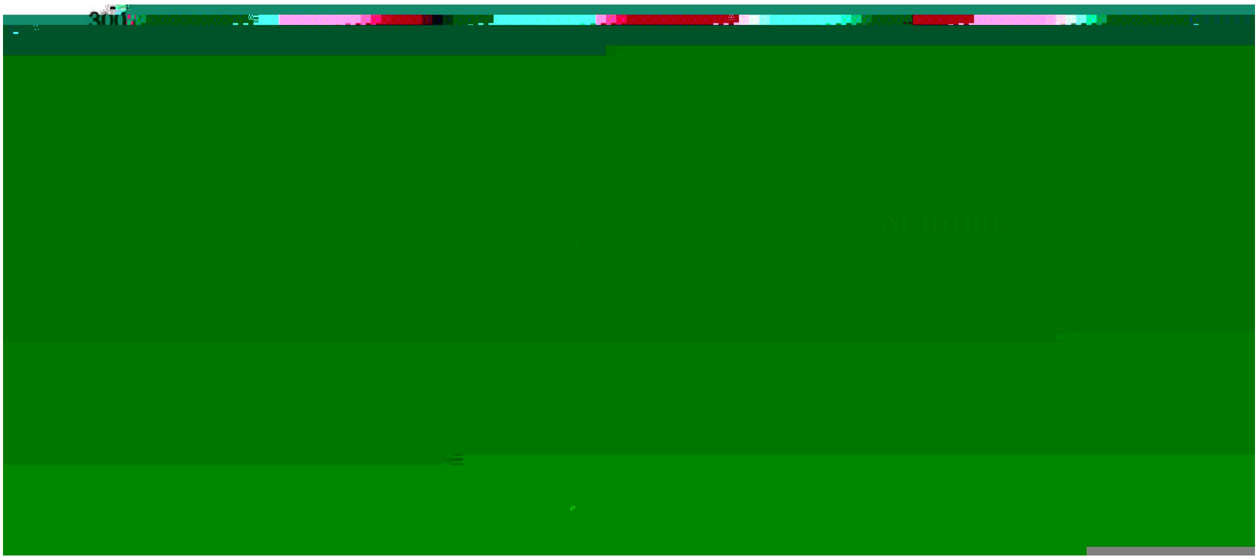
Note:

BR:	Company Code
MUR2060	Product Type.
****:	Lot No. Code, code change with Lot No.



Note:

1	25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量				Dimension 包装尺寸 (unit: mm^3)
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Box62.4 19(((K3(K)TT1/Ou(K4462o 0 6.48 247.74 231.0003 TmT24780 T(7)TET/TT13 1 T81.0003 0 6.48 222.3 283.0403 TmT0 Tw1a	